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Supplementary Note 1:

Temperature dependence of photocurrent and photovoltage

In this Supplementary information, we discuss the possible mechanism for temperature dependence of short-circuit photocurrent and open-circuit photovoltage under irradiation of CW light. Although we have not completely understood the temperature dependence of short-circuit photocurrent (Fig. 2c) and open-circuit photovoltage (Fig. 2d), here we first discuss the former on the basis of the data analysis and then discuss the latter with assuming an equivalent circuit.

Supplementary Figure 1 shows the data of short-circuit photocurrent as a function of temperature on a semi-logarithmic scale and their fitting to a thermionic emission model assuming the contact involves a Schottky barrier. The data are well fitted to the formula of

$$J = AT^2 \exp\left(-\frac{e\Phi_B}{kT}\right) \quad (1)$$

where *e* is the elementary charge, Φ_B the barrier height, *k* the Boltzmann constant, *T* temperature, and *A* the Richardson constant, resulting in $\Phi_B \sim 40$ meV. Considering its narrow bandgap of about 500 meV, the barrier height is within reasonable range. Therefore it is most likely that the short-circuit current is limited by the contact resistance due to a Schottky barrier.



Supplementary Figure 1 | Temperature dependence of short-circuit photocurrent on a semi-logarithmic scale. The black line is a result of the fitting by the thermionic emission model.

Having established a quasi-exponential temperature dependence of contact resistance, we now discuss the temperature dependence of the open-circuit photovoltage with assuming an equivalent circuit model. Supplementary Figure 2 displays the simplest equivalent circuit that may represent device condition during photovoltaic effect measurements, where I_{shift} is shift current which works as a current source, I_{obs} is an observed current, V is a voltage between two electrodes, and R^*_{bulk} and R^*_{contact} are bulk and contact resistances for photocurrent under illumination, respectively. These parameters are related by the following equation,

$$I_{\rm obs} = \frac{1}{R_{\rm bulk}^* + R_{\rm contact}^*} V + \frac{R_{\rm bulk}^*}{R_{\rm bulk}^* + R_{\rm contact}^*} I_{\rm shift} \quad (2) \,.$$

The open-circuit photovoltage (short-circuit photocurrent) is output voltage (current) when $I_{obs} = 0$ (V = 0). Then, V_{OC} and I_{SC} are given by

$$V_{\rm OC} = -R_{\rm bulk}^* I_{\rm shift} \quad (3) ,$$
$$I_{\rm SC} = \frac{R_{\rm bulk}^*}{R_{\rm bulk}^* + R_{\rm contact}^*} I_{\rm shift} \quad (4)$$

Suppose I_{shift} is temperature independent and $R^*_{\text{bulk}} \ll R^*_{\text{contact}}$, Eq. 4 implies that I_{SC} exponentially decays in low temperature as was shown in Supplementary Fig. 1, whereas Eq. 3 implies that V_{OC} is proportional to R^*_{bulk} which can have non-exponential temperature dependence.



Supplementary Figure 2 | An equivalent circuit for the sample condition during measurements of photovoltaic effect.